



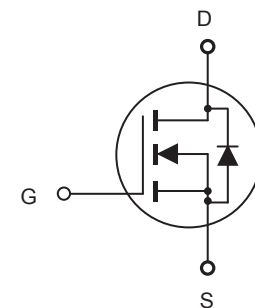
CED3100/CEU3100

N-Channel Enhancement Mode Field Effect Transistor

PRELIMINARY

FEATURES

- 30V, 51A, $R_{DS(ON)} = 10m\Omega$ @ $V_{GS} = 10V$.
 $R_{DS(ON)} = 17m\Omega$ @ $V_{GS} = 4.5V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead free product is acquired.
- TO-251 & TO-252 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	51	A
Drain Current-Pulsed ^a	I_{DM}	204	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ - Derate above 25°C	P_D	46	W
		0.36	W/ $^\circ\text{C}$
Operating and Store Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.7	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	$^\circ\text{C/W}$

This is preliminary information on a new product in development now .
Details are subject to change without notice .

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<http://www.cetsemi.com>



CED3100/CEU3100

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -20V, V_{DS} = 0V$			-100	nA
On Characteristics ^c						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1		3	V
Static Drain-Source	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		8	10	m Ω
On-Resistance		$V_{GS} = 4.5V, I_D = 15A$		12	17	m Ω
Dynamic Characteristics ^d						
Input Capacitance	C_{iss}	$V_{DS} = 15V, V_{GS} = 0V,$ $f = 1.0\text{ MHz}$		895		pF
Output Capacitance	C_{oss}			215		pF
Reverse Transfer Capacitance	C_{rss}			160		pF
Switching Characteristics ^d						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15V, I_D = 10A,$ $V_{GS} = 10V, R_{GEN} = 3\Omega$		11	22	ns
Turn-On Rise Time	t_r			7	14	ns
Turn-Off Delay Time	$t_{d(off)}$			31	62	ns
Turn-Off Fall Time	t_f			5	10	ns
Total Gate Charge	Q_g	$V_{DS} = 15V, I_D = 10A,$ $V_{GS} = 10V$		21	27	nC
Gate-Source Charge	Q_{gs}			2		nC
Gate-Drain Charge	Q_{gd}			6		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^b	I_S				51	A
Drain-Source Diode Forward Voltage ^c	V_{SD}	$V_{GS} = 0V, I_S = 20A$			1.2	V

Notes : □

a. Repetitive Rating : Pulse width limited by maximum junction temperature. □

b. Surface Mounted on FR4 Board, $t \leq 10\text{ sec.}$ □

c. Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. □

d. Guaranteed by design, not subject to production testing. □

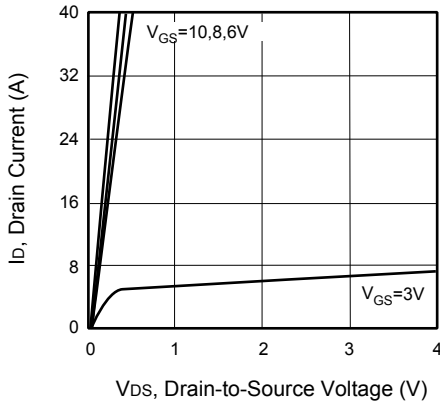


Figure 1. Output Characteristics

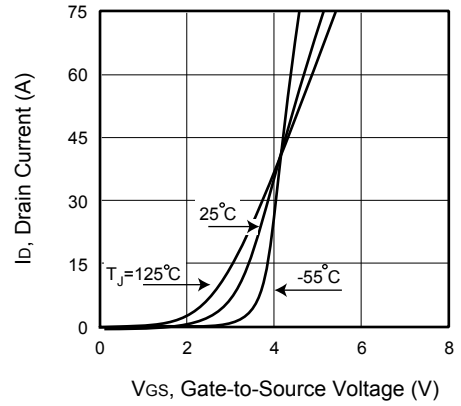


Figure 2. Transfer Characteristics

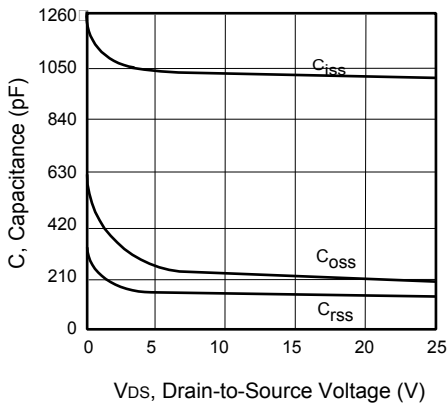


Figure 3. Capacitance

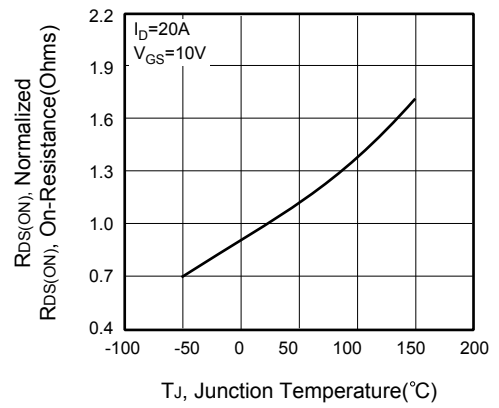


Figure 4. On-Resistance Variation with Temperature

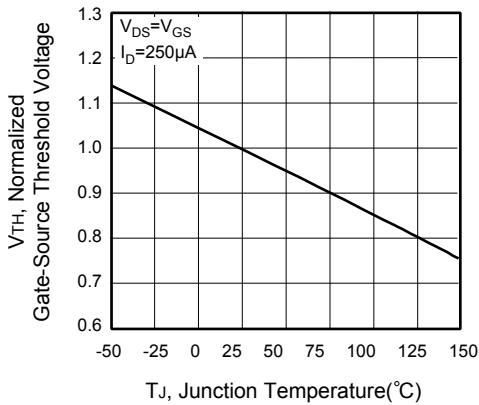


Figure 5. Gate Threshold Variation with Temperature

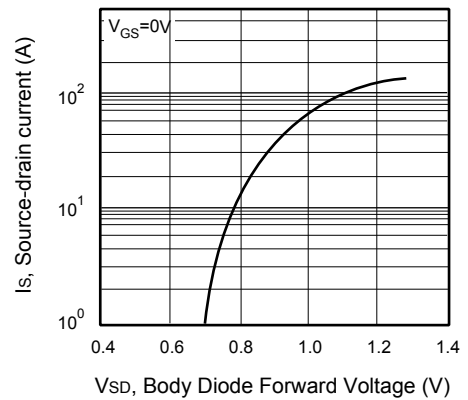


Figure 6. Body Diode Forward Voltage Variation with Source Current



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